

# **FIRST PRINCIPLES CALCULATIONS ON BORON SUBOXIDE( $B_6O$ )**

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# INTRODUCTION

- Boron Suboxide ( $B_6O$ ) is a boron-rich covalent ceramic known for its extreme hardness, low density, and excellent thermal stability.
- It is considered one of the hardest materials after diamond and cubic boron nitride.
- Theoretical (first-principles) calculations help us understand its crystal structure, bonding nature, electronic properties, and mechanical strength.

# WHY STUDY B<sub>6</sub>O?

- B<sub>6</sub>O exhibits a superhard nature (~45 GPa hardness) with a high melting point (>2000 °C).
- Its icosahedral boron framework imparts excellent strength and stiffness.
- Useful for abrasives, armor, and high-temperature structural components.

# ALPHA-B<sub>6</sub>O STRUCTURE

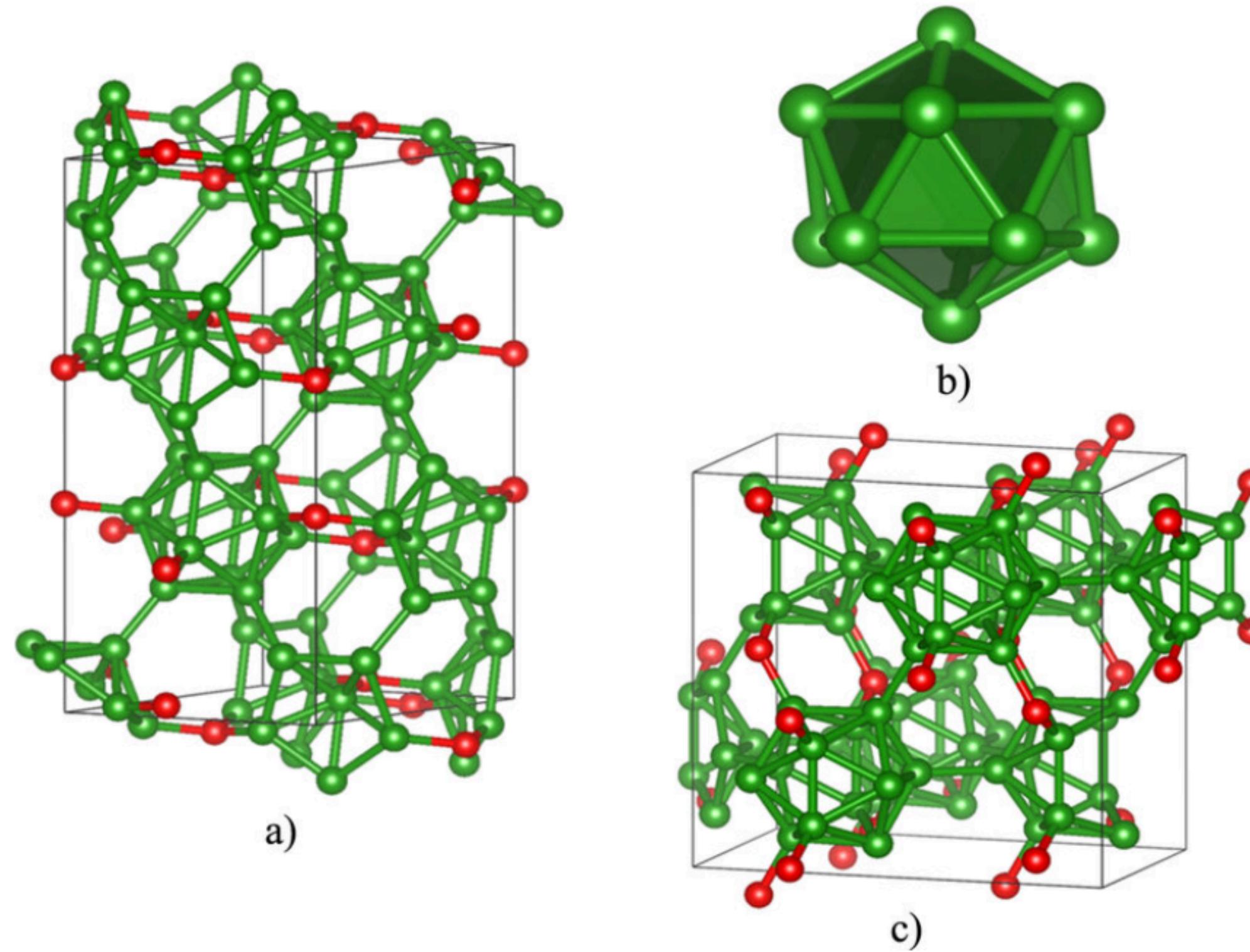
- Space group: R-3m (No. 166) (rhombohedral)
- Stoichiometry: B<sub>6</sub>O (36 B + 6 O in conventional hex cell; primitive rhombohedral cell descriptions exist).
- Typical bond lengths : **B–O ≈ 1.49 Å, O–O ≈ 3.08 Å**; internal **B–B** bonds inside icosahedra are **~1.69–1.78 Å** (varies locally)
- Structure is often described as “**oxygen-stuffed α-boron**”: a cubic-close-packing of B<sub>12</sub> icosahedra with oxygen atoms filling octahedral voids.

## BETA-B<sub>6</sub>O STRUCTURE

- $\beta$ -B<sub>6</sub>O was predicted in 2016 by Dong, Oganov as a new ground-state candidate.
- Space group: Cmcm (No. 63) (orthorhombic)
- In  $\beta$ , there is no simple close-packing sequence – icosahedra form a 3-D interconnected orthorhombic network contrasting  $\alpha$ 's ABC stacking.
- lattice parameters: **$a \approx 5.39 \text{ \AA}$ ,  $b \approx 8.78 \text{ \AA}$ ,  $c \approx 8.74 \text{ \AA}$**
- $\beta$ -B<sub>6</sub>O is slightly more stable than  $\alpha$  under ambient conditions .

# Alpha-B<sub>6</sub>O Structure

| Feature            | Rhombohedral Setting<br>(Primitive Cell)                               | Hexagonal Setting (Conventional Cell)  |
|--------------------|--|--|
| Crystal system     | Trigonal (Rhombohedral primitive)                                      | Trigonal expressed in hexagonal axes   |
| Space group        | R $\bar{3}m$ (No. 166)   | P1 (No. 1) - symmetry removed  |
| Cell type          | Primitive (rhombohedral)   | Conventional (hexagonal)   |
| Lattice Parameters | $a=b=c=5.137 \text{ \AA}$ ,<br>$\alpha = \beta = \gamma = 63.04^\circ$ | <b><math>a = b = 5.376 \text{ \AA}</math> ; <math>c = 12.276 \text{ \AA}</math> ; <math>\alpha = \beta = 90^\circ</math> ;<br/><math>\gamma = 120^\circ</math></b> |
| Atoms / cell       | 14 (12 B + 2 O) $\rightarrow$ 2 formula units                          | 42 (36 B + 6 O) $\rightarrow$ 6 formula units  |
| Cell Volume        | 102.43 $\text{\AA}^3$ (Exactly 1/3 of the hexagonal volume)            | 307.30 $\text{\AA}^3$  |

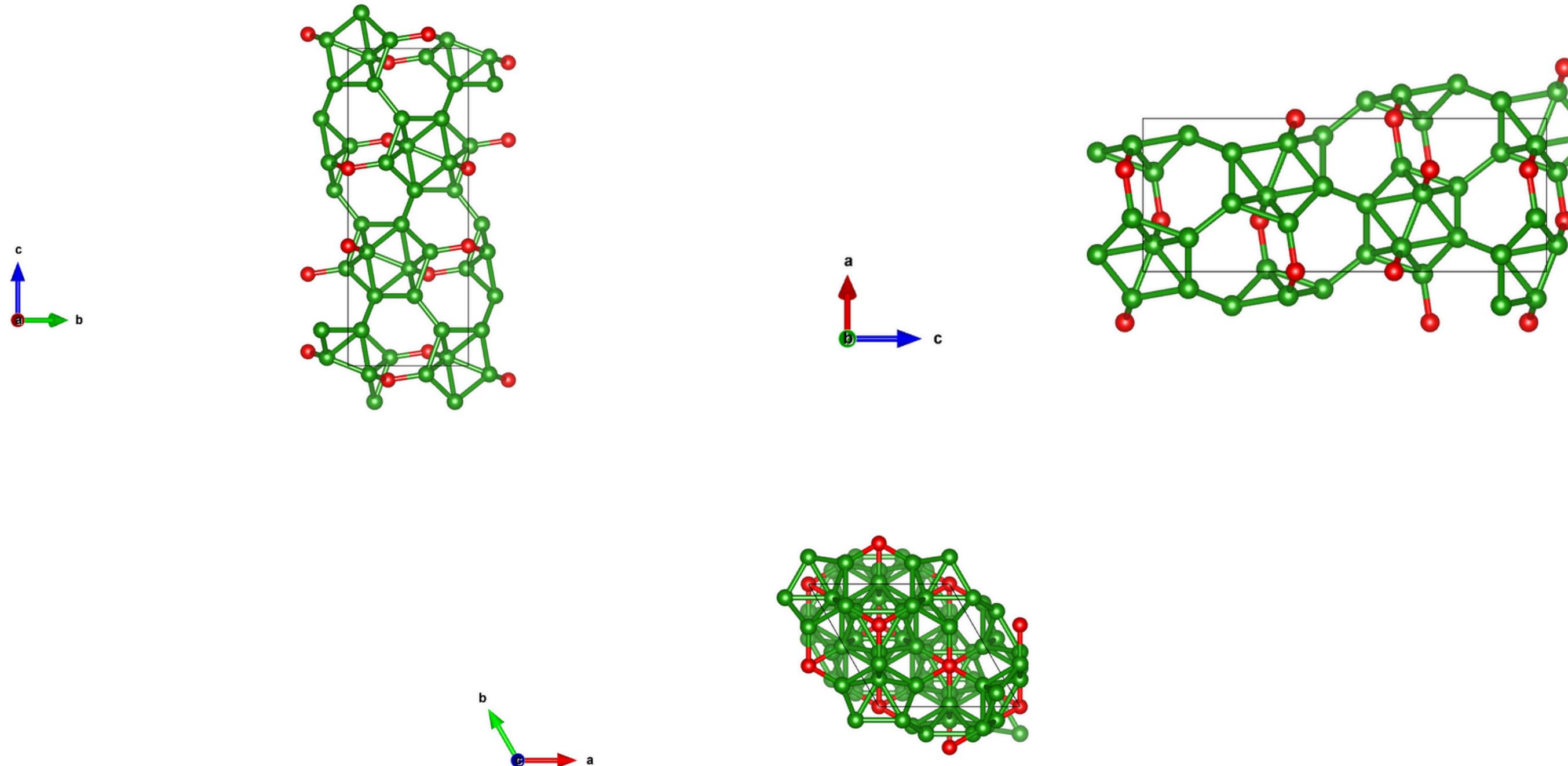


**Crystal structures of (a)  $\alpha$ -B<sub>6</sub>O; (b) B<sub>12</sub> icosahedra; (c)  $\beta$ -B<sub>6</sub>O. Green and red spheres denote boron and oxygen atoms, respectively.**

## COMPARISON OF ALPHA VS BETA (STRUCTURE & PROPERTIES)

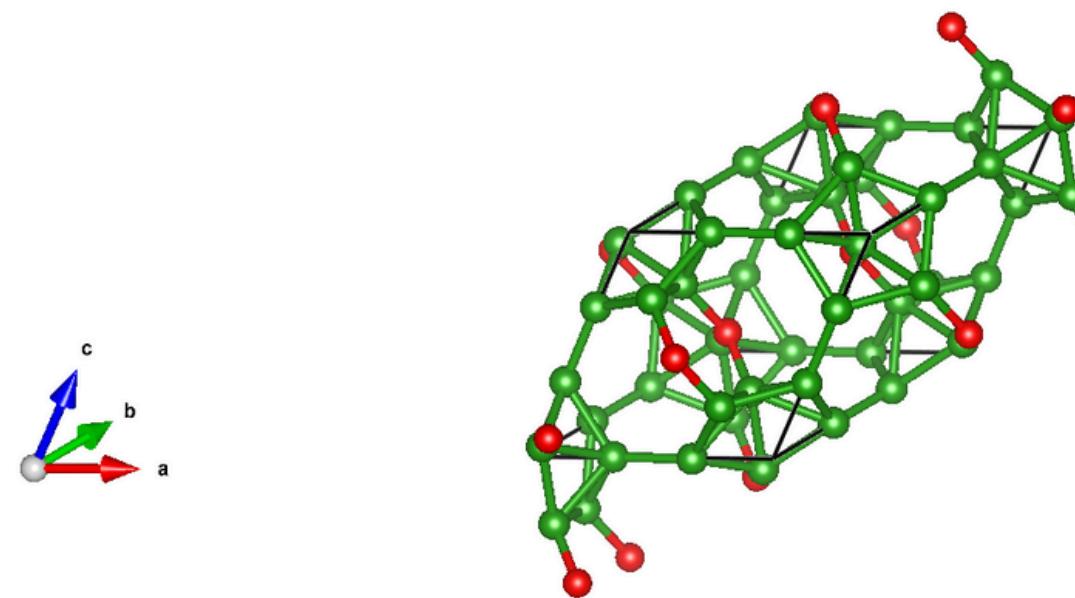
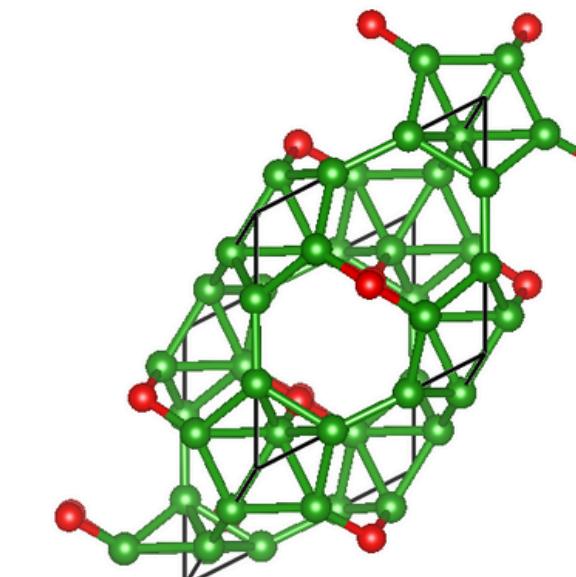
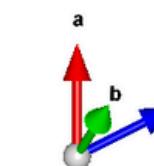
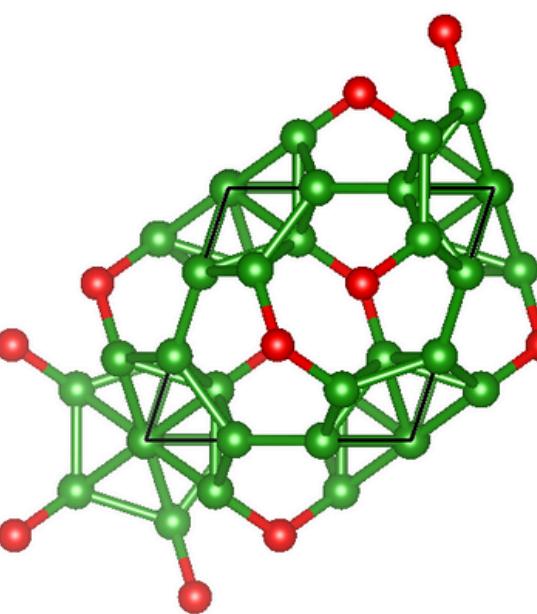
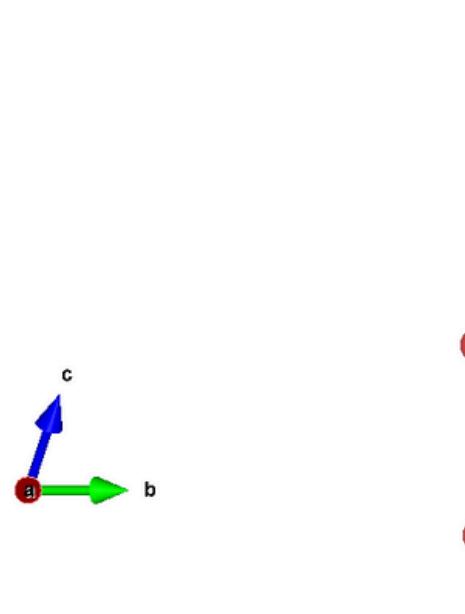
| Feature                | $\alpha\text{-B}_6\text{O}$       | $\beta\text{-B}_6\text{O}$  |
|------------------------|-----------------------------------|---|
| Space group            | R-3m                              | Cmcm  |
| Stacking of icosahedra | ABC (ccp)                         | Not a simple close-packing sequence – icosahedra form a 3-D interconnected orthorhombic network |
| Volume                 | $51.71 \text{ \AA}^3$             | $51.69 \text{ \AA}^3$   |
| Hardness (DFT)         | $\sim 38 \text{ GPa}$             | $\sim 39 \text{ GPa}$   |
| Band gap type          | Direct ( $\sim 1.85 \text{ eV}$ ) | Indirect ( $\sim 1.81 \text{ eV}$ )   |

# $\alpha$ -B<sub>6</sub>O: Hexagonal (Expanded P1) Representation



HEXAGONAL (CONVENTIONAL) SETTING

# Primitive $\alpha$ -B<sub>6</sub>O



| <b>Setting</b>                           | <b>Total Atoms</b> | <b>Wycoff Positions</b>  |
|--|--------------------|--|
| Hexagonal<br>Setting(Conventional)       | 42 ( $B_{36}O_6$ ) | <ul style="list-style-type: none"> <li>• O: 6c --- (1/3, 2/3, 0.044564)</li> <li>• <math>B_1</math>: 18h --- (0.491569, 0.508431, 0.307049)</li> <li>• <math>B_2</math>: 18h --- (0.443729, 0.556271, 0.554067)</li> </ul> |
| Rhombohedral Setting<br>(Primitive Cell) | 14 ( $B_{12}O_2$ ) | <ul style="list-style-type: none"> <li>• O: 2c</li> <li>• <math>B_1</math>: 6h</li> <li>• <math>B_2</math>: 6h</li> </ul>  |

# Part 1: Structural Relaxation

- **Objective:** To find the lowest-energy, stable ground-state structure of B<sub>6</sub>O.
- **Why?** This optimized structure is the required starting point for all other property calculations (DOS, Band Structure, and Elastic Properties).
- **Method:**
  - We start with an initial structure (POSCAR), in this case, the α-B<sub>6</sub>O example primitive cell from the Materials Project (mp-1346).
  - We use VASP to calculate the forces on all atoms and the stress on the lattice.
  - The calculation then moves the atoms and changes the cell shape/volume to minimize these forces and stresses, until a stable (converged) structure is found (CONTCAR).

## Part 2: Static SCF

- **What is this step?**

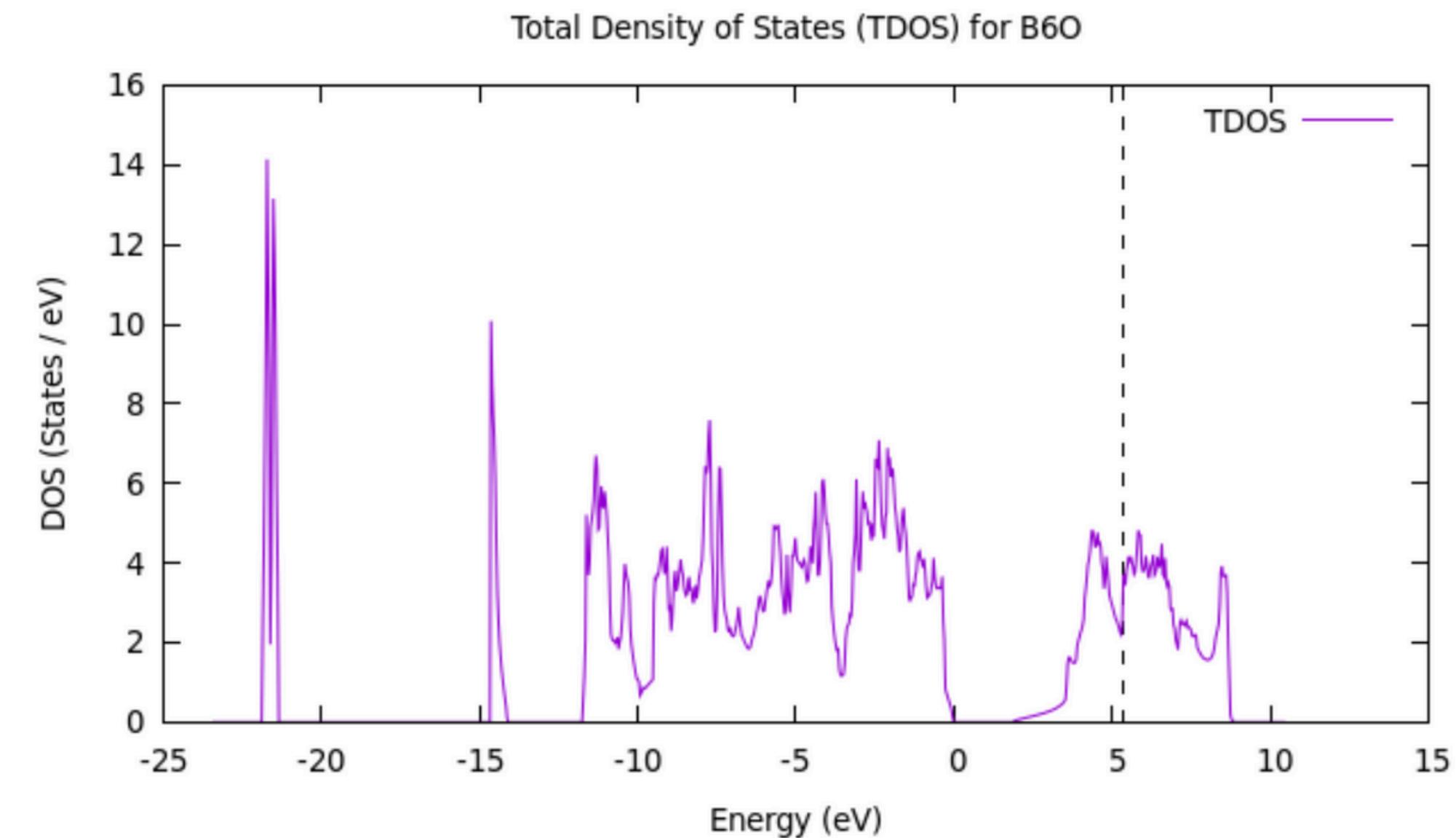
- A high-precision, static calculation is performed on the previously relaxed structure.
- "Static" means the atoms are held in their final, stable positions.
- A Self-Consistent Field (SCF) loop is run to find the precise, stable electronic ground state.
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- **Why is this done?**

- This is the primary "data collection" step for electronic properties.
- Its main purpose is to generate the high-resolution data needed for the Density of States (DOS).
- This static calculation provides a much more accurate and detailed electronic snapshot than is possible during the structural relaxation.

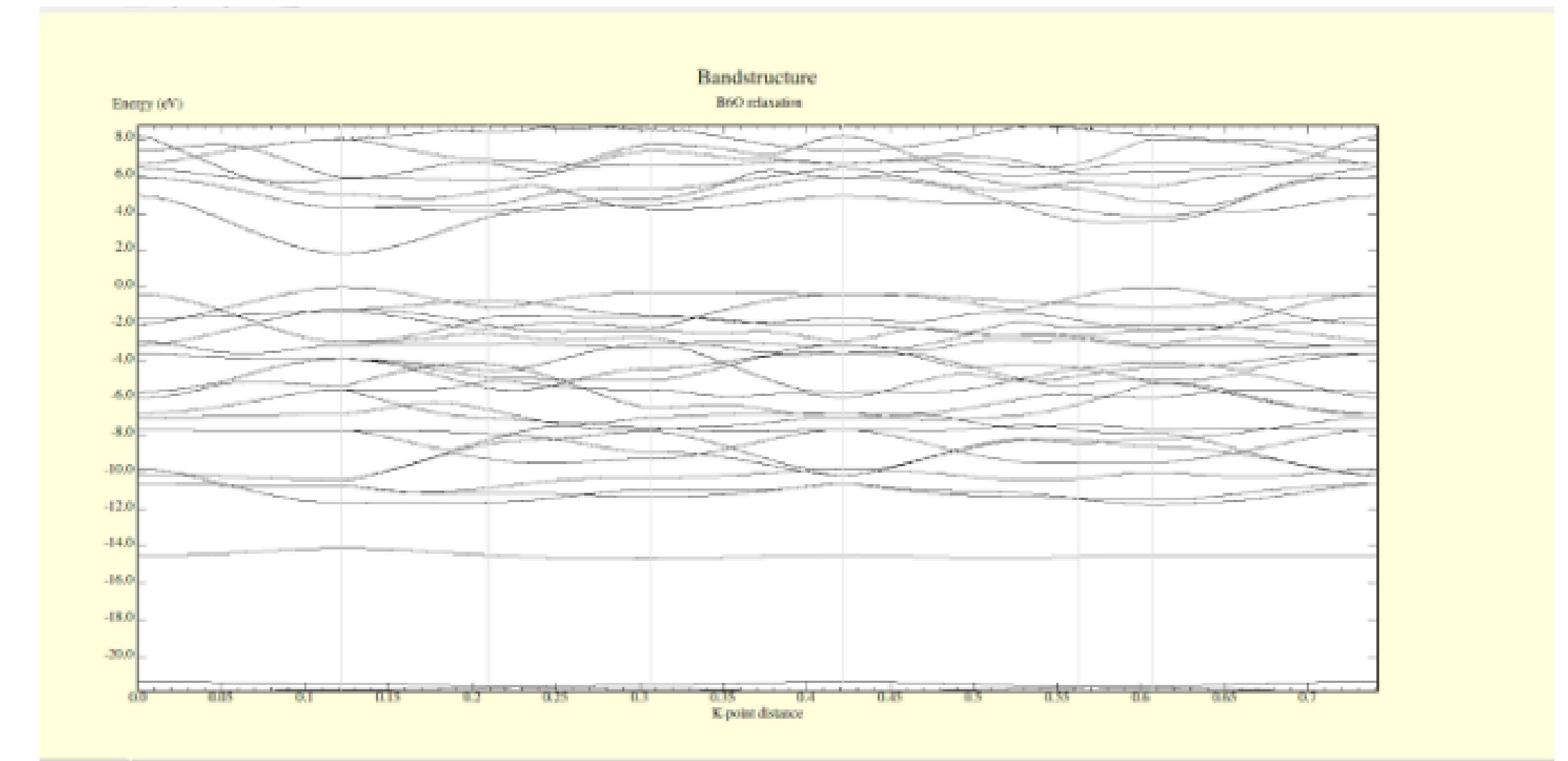
## Part 3: Density of States

- The DOS spectrum reveals the distribution of electronic states across energy levels for primitive B<sub>6</sub>O.
- A clear semiconducting nature is observed, with a distinct region of zero states near the Fermi level
- A strong, localized bonding peak appears near -22 eV, characteristic of deep B-O bonding states
- The Fermi level lies at 5.091 eV (shifted to 0 eV in the DOS plot for clarity).
- The DOS profile confirms strong covalent bonding and a stable electronic structure influenced by B<sub>12</sub> icosahedra.



## Part 4: Band Structure

- The calculated band structure of primitive  $B_6O$  shows a direct band gap.
- Band Gap: 1.8515 eV
- VBM (Valence Band Maximum):
  - Energy: 5.0872 eV
  - k-point: (0.5, 0.5, 0.5)
- CBM (Conduction Band Minimum):
  - Energy: 6.9387 eV
  - k-point: (0.5, 0.5, 0.5)



- The valence bands are relatively flat, showing localized bonding states due to strong B-O covalent interactions.
- The conduction bands are more dispersive, implying better electron mobility once excited.
- Overall, the band structure confirms that  $B_6O$  is a stable wide-gap semiconductor with strong covalent bonding.

# Elastic Properties

## What Are Elastic Constants ( $C_{ij}$ )?

- ( $C_{ij}$ ) are components of the stiffness tensor, describing how a material responds to stress.
- They relate stress and strain via Hooke's Law in tensor form:  $\sigma_i = \sum_j C_{ij} \epsilon_j$
- Determine stiffness, hardness, brittleness, sound velocity, and mechanical stability.

| $C_{ij}$ | 1       | 2       | 3       | 4       | 5       | 6       |
|----------|---------|---------|---------|---------|---------|---------|
| 1        | 584.826 | 123.839 | 49.848  | 0.000   | 22.694  | 0.000   |
| 2        | 123.839 | 584.826 | 49.848  | 0.000   | -22.694 | 0.000   |
| 3        | 49.848  | 49.848  | 458.097 | 0.000   | 0.000   | 0.000   |
| 4        | 0.000   | 0.000   | 0.000   | 230.493 | 0.000   | 22.694  |
| 5        | 22.694  | -22.694 | 0.000   | 0.000   | 178.115 | 0.000   |
| 6        | 0.000   | 0.000   | 0.000   | 22.694  | 0.000   | 178.115 |

# Comparison

| Property              | Calculated Value | Actual Value |
|-----------------------|------------------|--------------|
| Bulk Modulus (GPa)    | 227.4            | 237          |
| Shear Modulus (GPa)   | 207.6            | 210          |
| Young's Modulus (GPa) | 477.5            | 480          |
| Poisson Ratio         | 0.165            | 0.16         |
| Anisotropy (AU)       | 0.193            | 0.20         |
| Debye Temp. (K)       | 1633             | ~1600        |

Reference: Materials Project Entry MP-1986 ( $\alpha$ -B<sub>6</sub>O)

# Interpretation of Elastic Properties

- **High Bulk Modulus (227 GPa)**
  - Material is highly incompressible, showing very strong overall bonding strength
- **Large Shear Modulus (208 GPa)**
  - Indicates excellent resistance to shape deformation, a signature of superhard materials.
- **Very High Young's Modulus (477 GPa)**
  - Reflects extremely high stiffness; small strain is produced even under high stress.
  - Confirms strong directional covalent bonding.
- **Low Poisson Ratio (0.165)**
  - Characteristic of brittle materials.
- **High Debye Temperature (1633 K)**
  - Suggests strong atomic bonding and excellent thermal stability.
  - Also correlates with high hardness and low lattice vibrations.

# Conclusion

- Primitive  $B_6O$  shows a direct band gap (1.85 eV) and strong B–O covalent bonding, confirming stable semiconducting behavior.
- Mechanical results indicate very high stiffness, incompressibility, and shear resistance, characteristic of superhard materials.
- Overall,  $B_6O$  is a strong, stable, and high-performance material suitable for extreme mechanical and thermal applications.

## References

- 1) ResearchGate:** [https://www.researchgate.net/publication/252700902\\_Crystal\\_Structure\\_of\\_B6O](https://www.researchgate.net/publication/252700902_Crystal_Structure_of_B6O)
- 2) ARXIV:** <https://arxiv.org/abs/1604.00586>
- 3) Materials Project :** <https://materialsproject.org/materials/mp-1346>